

## **General Description**

The AO8810 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the small power switching and load switch applications. The meet the RoHS and Product requirement with full function reliability approved.

## **General Features**

 $V_{DS} = 20V I_D = 7A$ 

 $R_{DS(ON)}$  < 14m $\Omega$  @ V<sub>GS</sub>=4. 5V

 $R_{DS(ON)} < 17m\Omega @ V_{GS}=2.5V$ 

## Application

Battery protection

Load switch

Uninterruptible power supply

## Package Marking and Ordering Information

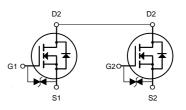
Product ID	Pack	Marking	Qty(PCS)
AO8810	TSSOP-8	8814	5000

#### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

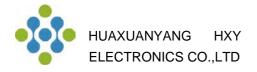
Symbol	Parameter	Limit	Unit	
V <sub>DS</sub>	Drain-Source Voltage	20	V	
V <sub>GS</sub>	Gate-Source Voltage	±10	V	
I <sub>D</sub>	Drain Current-Continuous	7	A	
Ідм	Drain Current-Pulsed (Note 1)	23	A	
PD	Maximum Power Dissipation	1.25	W	
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	111	°C <b>/W</b>	



TSSOP-8



**Dual N-Channel MOSFET** 



# Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	20	-	-	V
Zero Gate Voltage Drain Current	ldss	V <sub>DS</sub> =16V,V <sub>GS</sub> =0V			1	μA
Gate-Body Leakage Current	lgss	$V_{GS}=\pm 8V, V_{DS}=0V$			±100	nA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.5	0.7	1.2	V
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.5A	-	12	14	mΩ
Drain-Source On-State Resistance	Rds(on)	V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.5A	-	15	17	mΩ
Forward Transconductance	gfs	V <sub>DS</sub> =5V,I <sub>D</sub> =3.5A	-	20	-	S
Input Capacitance	Clss		-	955	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =8V,V <sub>GS</sub> =0V,	-	200	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	150	-	PF
Turn-on Delay Time	td(on)		-	8		nS
Turn-on Rise Time	tr	V <sub>DD</sub> =10V,I <sub>D</sub> =3.5A	-	17	-	nS
Turn-Off Delay Time	td(off)	$V_{\text{DD}}$ = 10V,1D=3.5A $V_{\text{GS}}$ =4.5V,R <sub>GEN</sub> =6Ω	-	27	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8.8	-	nS
Total Gate Charge	Qg		-	11.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =7A,	-	1.89	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =4.5V	-	3.56	-	nC
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	ls		-	-	7	A

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

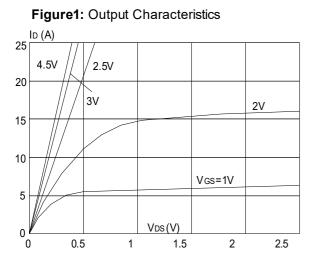
**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

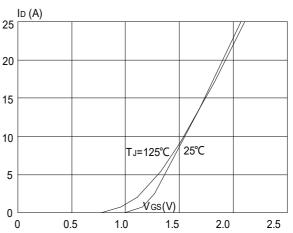
**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production

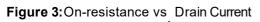


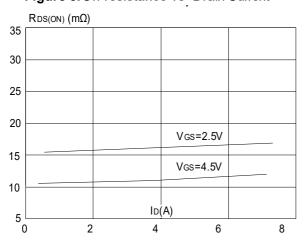
# **Typical Characteristics**

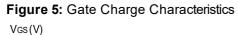




#### Figure 2: Typical Transfer Characteristics







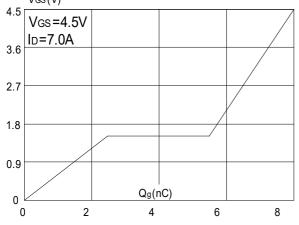
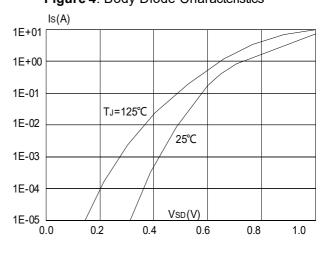
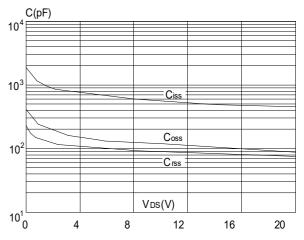
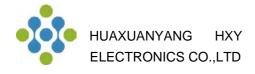


Figure 4: Body Diode Characteristics





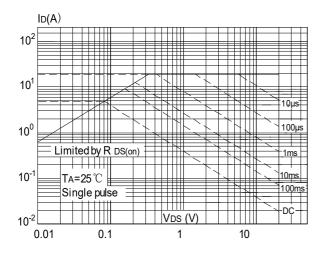


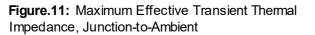


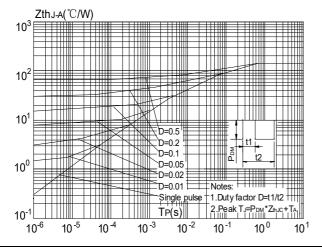
AO8810
Dual N-Channel Enhancement Mode MOSFET

Figure 7: Normalized Breakdown Voltage vs.

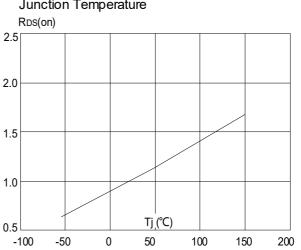
Figure 9: Maximum Safe Operating Area





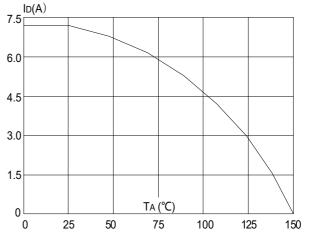


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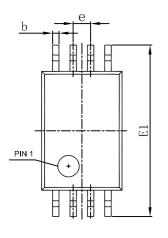
**Figure 8:** Normalized on Resistance vs. Junction Temperature

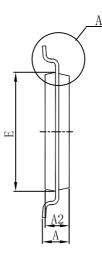


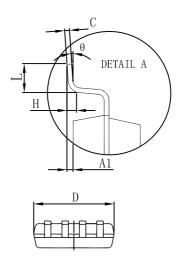




# **TSSOP-8** Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
D	2.900	3.100	0.114	0.122	
Е	4.300	4.500	0.169	0.177	
b	0.190	0.300	0.007	0.012	
с	0.090	0.200	0.004	0.008	
E1	6.250	6.550	0.246	0.258	
Α		1.200		0.047	
A2	0.800	1.000	0.031	0.039	
A1	0.050	0.150	0.002	0.006	
e	0.65 (BSC)		0. 026 (BSC)		
L	0.500	0.700	0.020	0.028	
Н	0.25(TYP)		0.01(TYP)		
θ	1°	7 °	1°	7 °	



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